

# BLF7G24L-140; BLF7G24LS-140

Power LDMOS transistor

Rev. 3 — 1 August 2011

Product data sheet

## 1. Product profile

### 1.1 General description

140 W LDMOS power transistor for base station applications at frequencies from 2300 MHz to 2400 MHz.

**Table 1. Typical performance**

Typical RF performance at  $T_{case} = 25\text{ °C}$  in a common source class-AB production test circuit.

Mode of operation	f (MHz)	$I_{DQ}$ (mA)	$V_{DS}$ (V)	$P_{L(AV)}$ (W)	$G_p$ (dB)	$\eta_D$ (%)	ACPR <sub>885k</sub> (dBc)	ACPR <sub>5M</sub> (dBc)
IS-95	2300 to 2400	1300	28	30	18.5	26.5	-45 <sup>[1]</sup>	
1 carrier W-CDMA	2300 to 2400	1300	28	50	18.5	33	-	-35 <sup>[2]</sup>

[1] Single carrier IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 - 13). PAR = 9.7 dB at 0.01 % probability on the CCDF. Channel bandwidth is 1.2288 MHz.

[2] 3GPP; test model 1; 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF. Channel bandwidth is 3.84 MHz.

### 1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low  $R_{th}$  providing excellent thermal stability
- Designed for low memory effects providing excellent digital pre-distortion capability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

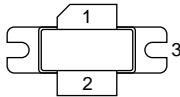
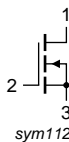
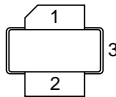

### 1.3 Applications

- RF power amplifiers for base stations and multi carrier applications in the 2300 MHz to 2400 MHz frequency range



## 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
BLF7G24L-140 (SOT502A)			
1	drain		
2	gate		
3	source		
BLF7G24LS-140 (SOT502B)			
1	drain		
2	gate		
3	source		

[1] Connected to flange.

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF7G24L-140	-	flanged LDMOST ceramic package; 2 mounting holes; 2 leads	SOT502A
BLF7G24LS-140	-	earless flanged LDMOST ceramic package; 2 leads	SOT502B

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	65	V
$V_{GS}$	gate-source voltage		-0.5	+13	V
$I_D$	drain current		-	28	A
$T_{stg}$	storage temperature		-65	+150	°C
$T_j$	junction temperature		-	200	°C

## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	$T_{case} = 80\text{ °C}$ ; $P_L = 125\text{ W}$	0.28	K/W

## 6. Characteristics

**Table 6. Characteristics**

$T_j = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0\text{ V}; I_D = 1\text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10\text{ V}; I_D = 216\text{ mA}$	1.5	1.8	2.3	V
$I_{DSS}$	drain leakage current	$V_{GS} = 0\text{ V}; V_{DS} = 28\text{ V}$	-	-	5	$\mu\text{A}$
$I_{DSX}$	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75\text{ V};$ $V_{DS} = 10\text{ V}$	34	42	-	A
$I_{GSS}$	gate leakage current	$V_{GS} = 11\text{ V}; V_{DS} = 0\text{ V}$	-	-	500	nA
$g_{fs}$	forward transconductance	$V_{DS} = 10\text{ V}; I_D = 216\text{ mA}$	-	1.87	-	S
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75\text{ V};$ $I_D = 7.56\text{ A}$	-	69	-	$\text{m}\Omega$

## 7. Test information

**Remark:** All testing performed in a class-AB production test circuit.

**Table 7. Functional test information**

Mode of operation: 1-carrier N-CDMA, single carrier IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 - 13). PAR = 9.7 dB at 0.01 % probability on the CCDF, channel bandwidth is 1.2288 MHz;  $f_1 = 2300\text{ MHz}$ ;  $f_2 = 2400\text{ MHz}$ ; RF performance at  $V_{DS} = 28\text{ V}$ ;  $I_{DQ} = 1300\text{ mA}$ ;  $T_{case} = 25\text{ }^{\circ}\text{C}$ ; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$P_{L(AV)}$	average output power		-	30	-	W
$G_p$	power gain		17.5	18.5	-	dB
$RL_{in}$	input return loss		-	-12	-	dB
$\eta_D$	drain efficiency		23	26.5	-	%
$ACPR_{885k}$	adjacent channel power ratio (885 kHz)		-	-45	-40	dBc

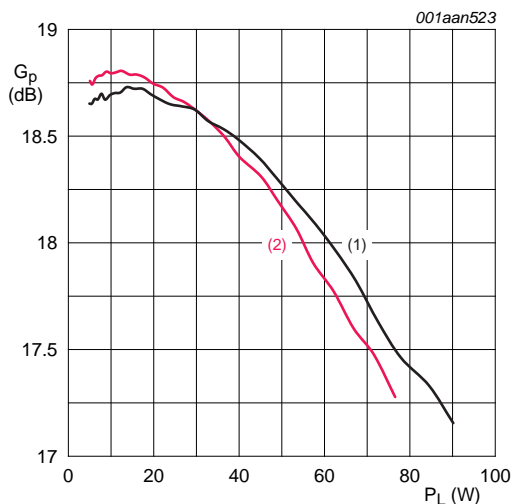
### 7.1 Ruggedness in class-AB operation

The BLF7G24L-140 and BLF7G24LS-140 are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:

$V_{DS} = 28\text{ V}$ ;  $I_{DQ} = 1300\text{ mA}$ ;  $P_L = 140\text{ W}$  (CW);  $f = 2300\text{ MHz}$ .

## 7.2 Single carrier IS-95

Single carrier IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 - 13).  
PAR = 9.7 dB at 0.01 % probability on the CCDF. Channel bandwidth is 1.2288 MHz

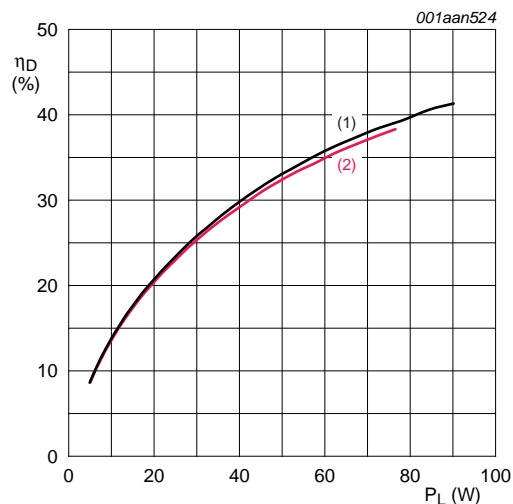


$V_{DS} = 28\text{ V}$ ;  $I_{DQ} = 1300\text{ mA}$ .

(1)  $f = 2300\text{ MHz}$

(2)  $f = 2400\text{ MHz}$

**Fig 1. Single carrier IS-95 power gain as a function of load power; typical values**

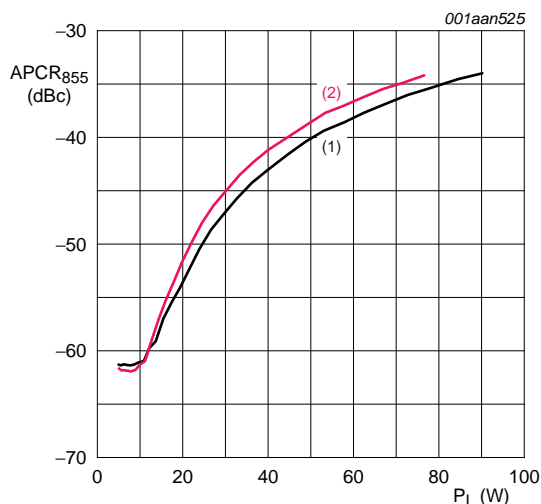


$V_{DS} = 28\text{ V}$ ;  $I_{DQ} = 1300\text{ mA}$ .

(1)  $f = 2300\text{ MHz}$

(2)  $f = 2400\text{ MHz}$

**Fig 2. Single carrier IS-95 drain efficiency as a function of load power; typical values**

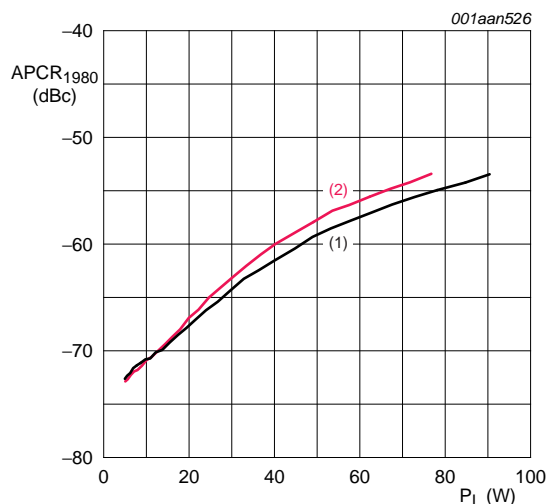


$V_{DS} = 28\text{ V}$ ;  $I_{DQ} = 1300\text{ mA}$ .

(1)  $f = 2300\text{ MHz}$

(2)  $f = 2400\text{ MHz}$

**Fig 3. Single carrier IS-95 ACPR at 885 kHz as a function of load power; typical values**

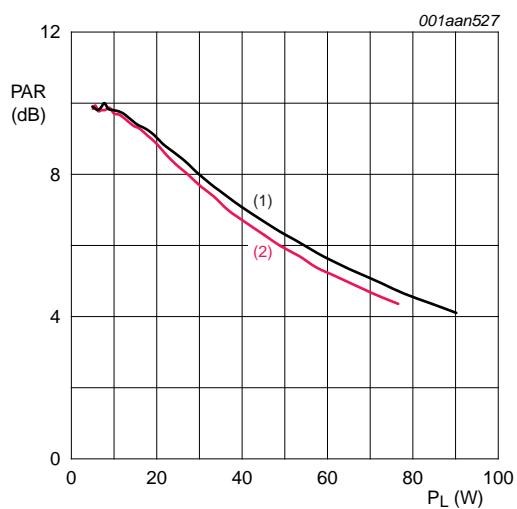


$V_{DS} = 28\text{ V}$ ;  $I_{DQ} = 1300\text{ mA}$ .

(1)  $f = 2300\text{ MHz}$

(2)  $f = 2400\text{ MHz}$

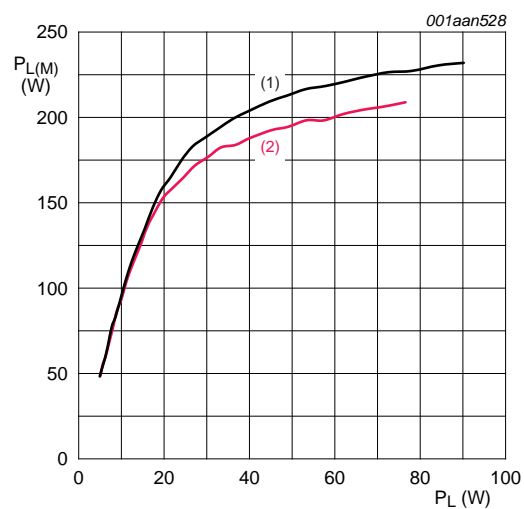
**Fig 4. Single carrier IS-95 ACPR at 1980 kHz as a function of load power; typical values**



$V_{DS} = 28 \text{ V}$ ;  $I_{DQ} = 1300 \text{ mA}$ .

- (1)  $f = 2300 \text{ MHz}$
- (2)  $f = 2400 \text{ MHz}$

**Fig 5. Single carrier IS-95 peak-to-average power ratio as a function of load power; typical values**

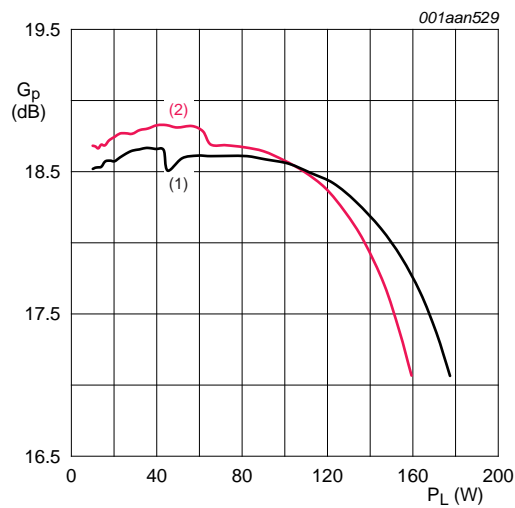


$V_{DS} = 28 \text{ V}$ ;  $I_{DQ} = 1300 \text{ mA}$ .

- (1)  $f = 2300 \text{ MHz}$
- (2)  $f = 2400 \text{ MHz}$

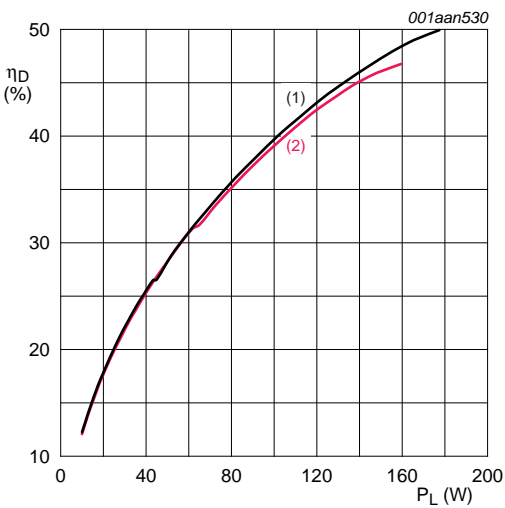
**Fig 6. Single carrier IS-95 peak power as a function of load power; typical values**

7.3 Pulsed CW



$V_{DS} = 28$  V;  $I_{Dq} = 1300$  mA.  
(1)  $f = 2300$  MHz  
(2)  $f = 2400$  MHz

Fig 7. Pulsed CW power gain as a function of load power; typical values

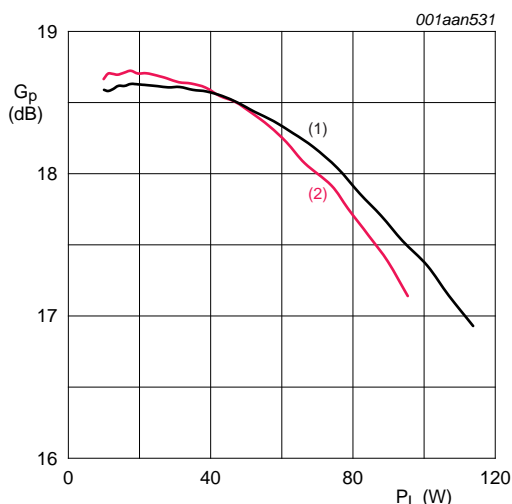


$V_{DS} = 28$  V;  $I_{Dq} = 1300$  mA.  
(1)  $f = 2300$  MHz  
(2)  $f = 2400$  MHz

Fig 8. Pulsed CW drain efficiency as a function of load power; typical values

## 7.4 Single carrier W-CDMA

3GPP; test model 1; 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF. Channel bandwidth is 3.84 MHz.

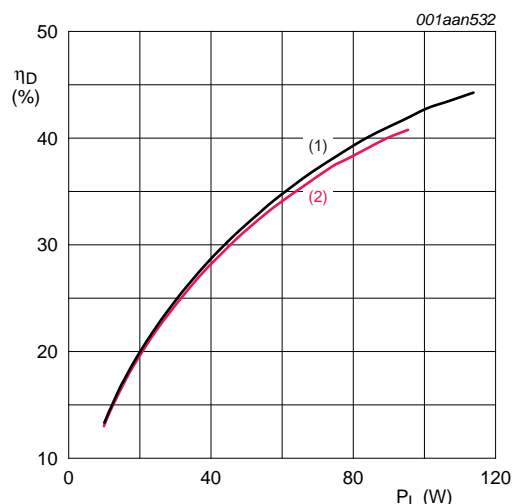


$V_{DS} = 28\text{ V}$ ;  $I_{DQ} = 1300\text{ mA}$ .

(1)  $f = 2300\text{ MHz}$

(2)  $f = 2400\text{ MHz}$

**Fig 9. Single carrier W-CDMA power gain as a function of load power; typical values**

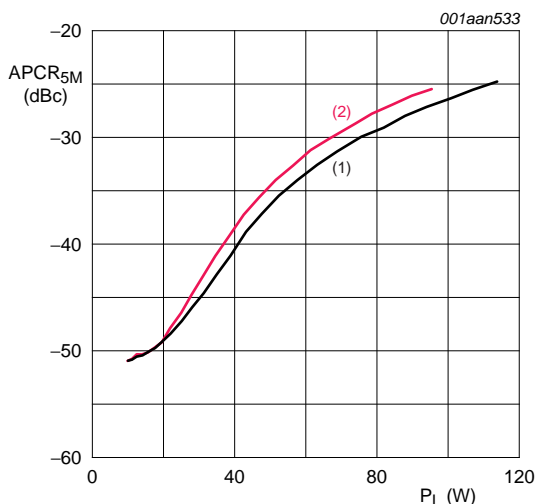


$V_{DS} = 28\text{ V}$ ;  $I_{DQ} = 1300\text{ mA}$ .

(1)  $f = 2300\text{ MHz}$

(2)  $f = 2400\text{ MHz}$

**Fig 10. Single carrier W-CDMA drain efficiency as a function of load power; typical values**

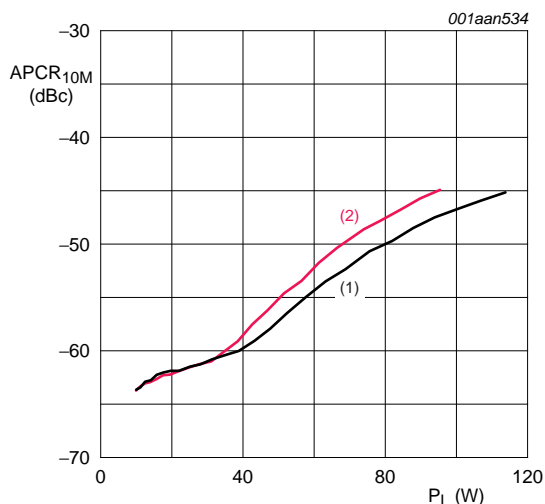


$V_{DS} = 28\text{ V}$ ;  $I_{DQ} = 1300\text{ mA}$ .

(1)  $f = 2300\text{ MHz}$

(2)  $f = 2400\text{ MHz}$

**Fig 11. Single carrier W-CDMA ACPR at 5 MHz as a function of load power; typical values**

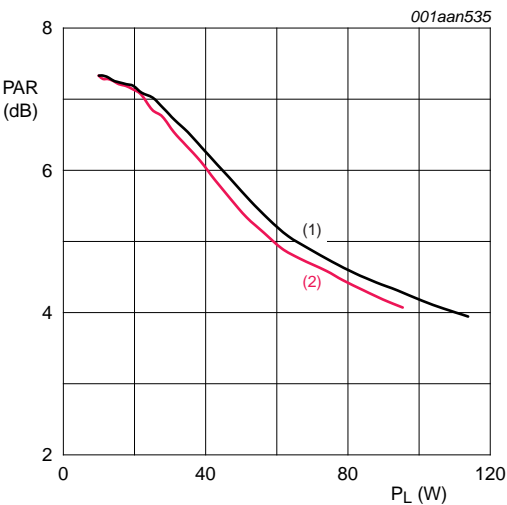


$V_{DS} = 28\text{ V}$ ;  $I_{DQ} = 1300\text{ mA}$ .

(1)  $f = 2300\text{ MHz}$

(2)  $f = 2400\text{ MHz}$

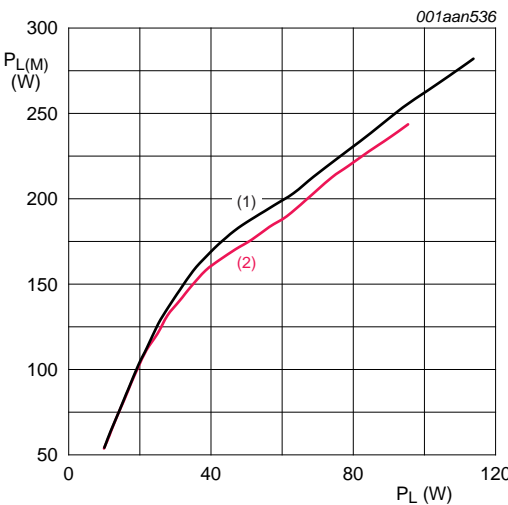
**Fig 12. Single carrier W-CDMA ACPR at 10 MHz as a function of load power; typical values**



$V_{DS} = 28$  V;  $I_{DQ} = 1300$  mA.

- (1)  $f = 2300$  MHz
- (2)  $f = 2400$  MHz

Fig 13. Single carrier W-CDMA peak-to-average power ratio as a function of load power; typical values



$V_{DS} = 28$  V;  $I_{DQ} = 1300$  mA.

- (1)  $f = 2300$  MHz
- (2)  $f = 2400$  MHz

Fig 14. Single carrier W-CDMA peak output power as a function of load power; typical values



8. Package outline

Flanged LDMOST ceramic package; 2 mounting holes; 2 leads

SOT502A

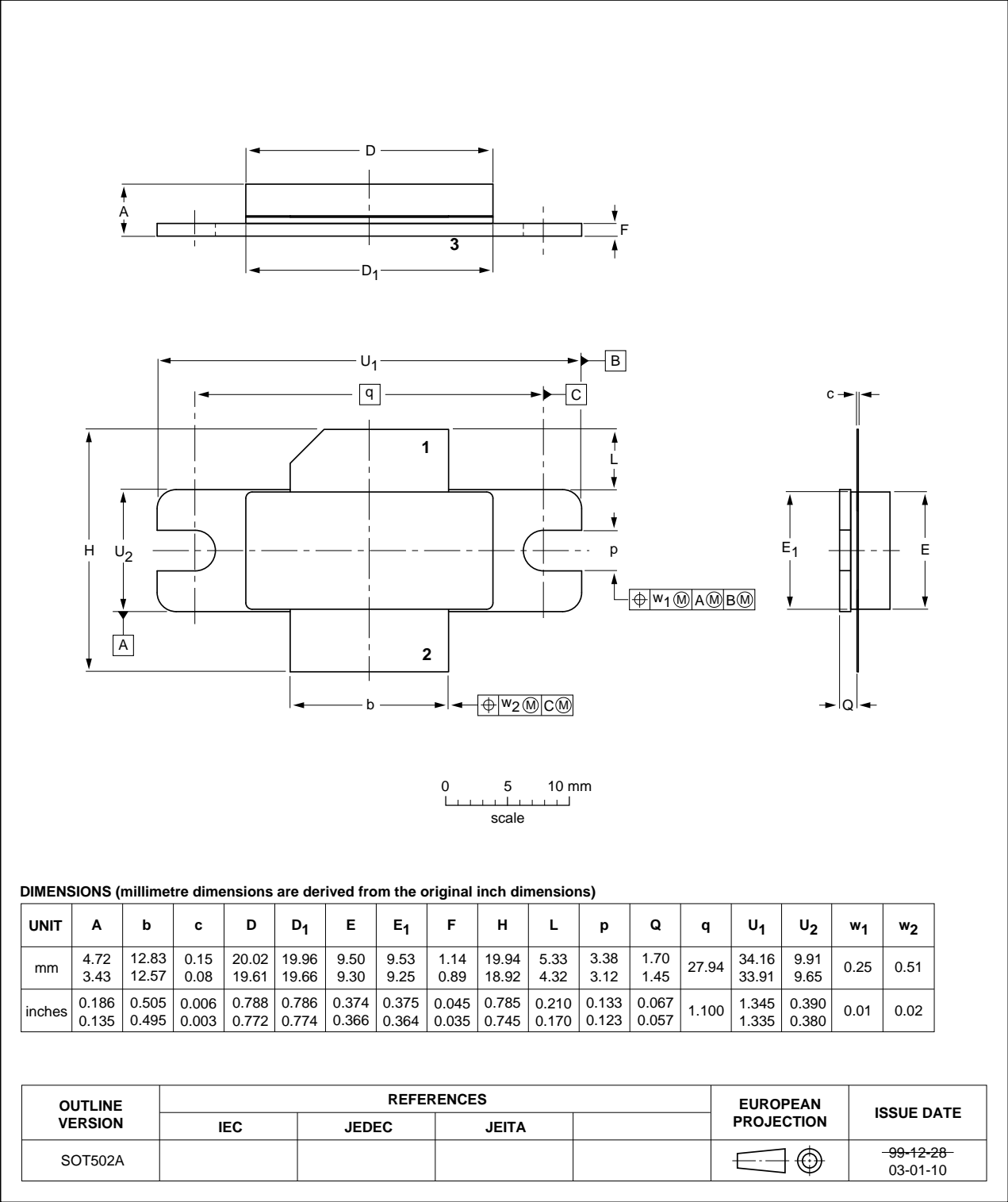


Fig 15. Package outline SOT502A

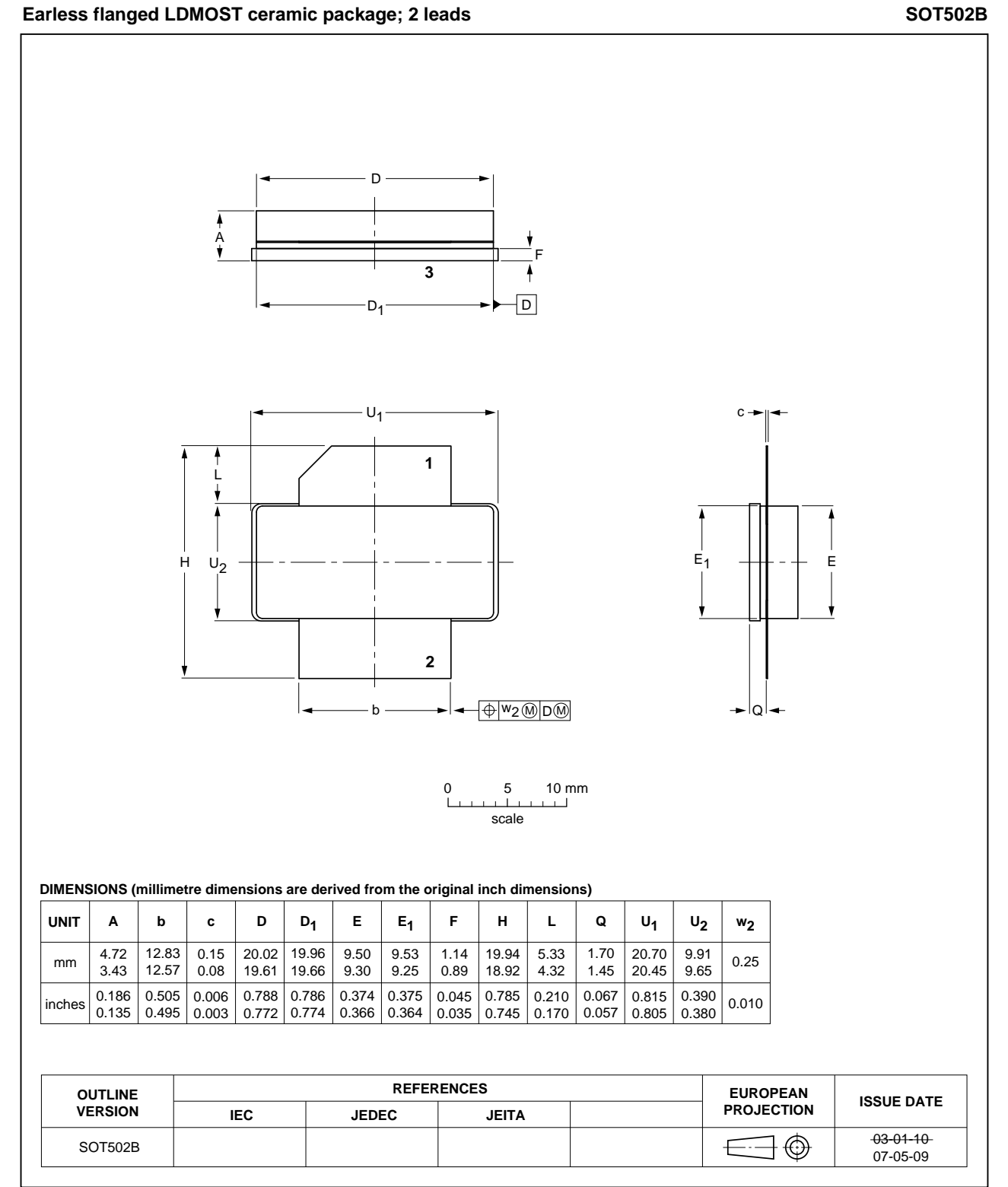


Fig 16. Package outline SOT502B

## 9. Abbreviations

**Table 8. Abbreviations**

Acronym	Description
3GPP	Third Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
IS-95	Interim Standard 95
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal Oxide Semiconductor
LDMOST	Laterally Diffused Metal Oxide Semiconductor Transistor
N-CDMA	Narrowband Code Division Multiple Access
PAR	Peak-to-Average power Ratio
RF	Radio Frequency
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

## 10. Revision history

**Table 9. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF7G24L-140_7G24LS-140 v.3	20110801	Product data sheet	-	BLF7G24L-140_7G24LS-140 v.2
Modifications:	• The status of this data sheet has been changed to Product data sheet			
BLF7G24L-140_7G24LS-140 v.2	20110405	Preliminary data sheet	-	BLF7G24L-140_7G24LS-140 v.1
BLF7G24L-140_7G24LS-140 v.1	20100805	Objective data sheet	-	-

## 11. Legal information

### 11.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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